Complementary Silicon Plastic Power Transistors

- . . . designed for use in general-purpose amplifier and switching applications.
- DC Current Gain Specified to 7.0 Amperes

 $h_{FE} = 30-150 @ I_C = 3.0 Adc - 2N6111, 2N6288$

= 2.3 (Min) @ I_C = 7.0 Adc — All Devices

• Collector-Emitter Sustaining Voltage -

VCEO(sus) = 30 Vdc (Min) — 2N6111, 2N6288

= 50 Vdc (Min) — 2N6109

= 70 Vdc (Min) — 2N6107, 2N6292

• High Current Gain — Bandwidth Product

f_T = 4.0 MHz (Min) @ I_C = 500 mAdc — 2N6288, 90, 92

= 10 MHz (Min) @ I_C = 500 mAdc — 2N6107, 09, 11

• TO-220AB Compact Package

*MAXIMUM RATINGS

Rating	Symbol	2N6111 2N6288	2N6109	2N6107 2N6292	Unit
Collector–Emitter Voltage	VCEO	30	50	70	Vdc
Collector-Base Voltage	VCB	40	60	80	Vdc
Emitter-Base Voltage	VEB	5.0			Vdc
Collector Current — Continuous Peak	IC	7.0 10		Adc	
Base Current	ΙΒ	3.0		Adc	
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	40 0.32		Watts W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150		°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	3.125	°C/W

^{*} Indicates JEDEC Registered Data.

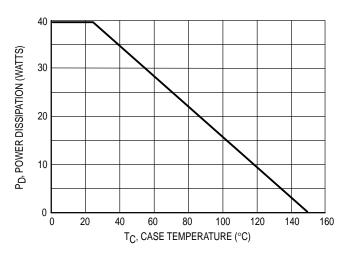


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

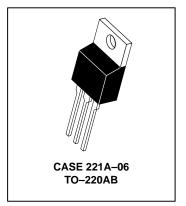
REV 2

2N6057 thru 2N6059 (See 2N6050)

2N6107 2N6109* 2N6111 2N6288

*Motorola Preferred Device

7 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
30-50-70 VOLTS
40 WATTS





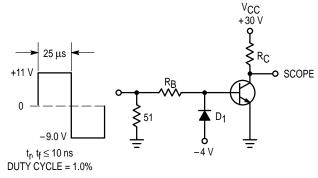
2N6107 2N6109 2N6111 2N6288 2N6292

*ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•			
Collector–Emitter Sustaining Voltage (1) (I _C = 100 mAdc, I _B = 0)	2N6111, 2N6288 2N6109 2N6107, 2N6292	VCEO(sus)	30 50 70	_ _ _	Vdc
Collector Cutoff Current (VCE = 20 Vdc, IB = 0) (VCE = 40 Vdc, IB = 0) (VCE = 60 Vdc, IB = 0)	2N6111, 2N6288 2N6109 2N6107, 2N6292	ICEO	_ _ _	1.0 1.0 1.0	mAdc
Collector Cutoff Current (VCE = 40 Vdc, VEB(off) = 1.5 Vdc) (VCE = 60 Vdc, VEB(off) = 1.5 Vdc) (VCE = 80 Vdc, VEB(off) = 1.5 Vdc) (VCE = 30 Vdc, VEB(off) = 1.5 Vdc, T _C = 150°C) (VCE = 50 Vdc, V _E (off) = 1.5 Vdc, T _C = 150°C) (VCE = 70 Vdc, V _E (off) = 1.5 Vdc, T _C = 150°C)	2N6111, 2N6288 2N6109 2N6107, 2N6292 2N6111, 2N6288 2N6109 2N6107, 2N6292	ICEX	_ _ _ _ _	100 100 100 2.0 2.0 2.0	μAdc mAdc
Emitter Cutoff Current (VBE = 5.0 Vdc, I _C = 0)		I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS (1)					
DC Current Gain (IC = 2.0 Adc, VCE = 4.0 Vdc) (IC = 2.5 Adc, VCE = 4.0 Vdc) (IC = 3.0 Adc, VCE = 4.0 Vdc) (IC = 7.0 Adc, VCE = 4.0 Vdc)	2N6107, 2N6292 2N6109 2N6111, 2N6288 All Devices	hFE	30 30 30 2.3	150 150 150 —	
Collector–Emitter Saturation Voltage (I _C = 7.0 Adc, I _B = 3.0 Adc)		VCE(sat)	_	3.5	Vdc
Base–Emitter On Voltage (I _C = 7.0 Adc, V _{CE} = 4.0 Vdc)		V _{BE(on)}	_	3.0	Vdc
DYNAMIC CHARACTERISTICS		•		•	
Current Gain — Bandwidth Product (2) ($I_C = 500 \text{ mAdc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 1.0 \text{ MHz})$	2N6288, 92 2N6107, 09, 11	fΤ	4.0 10		MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{ob}	_	250	pF
Small–Signal Current Gain (IC = 0.5 Adc, V_{CE} = 4.0 Vdc, f =	= 50 kHz)	h _{fe}	20	_	_

^{*} Indicates JEDEC Registered Data.

⁽²⁾ $f_T = |h_{fe}| \bullet f_{test}$.



 R_B and R_C ARE VARIED TO OBTAIN DESIRED CURRENT LEVELS

D1 MUST BE FAST RECOVERY TYPE, eg: 1N5825 USED ABOVE $I_B \approx 100$ mA MSD6100 USED BELOW $I_B \approx 100$ mA

Figure 2. Switching Time Test Circuit

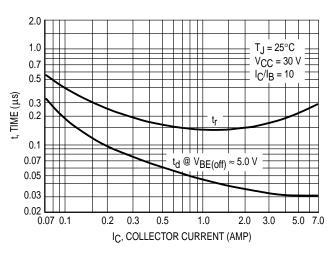


Figure 3. Turn-On Time

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

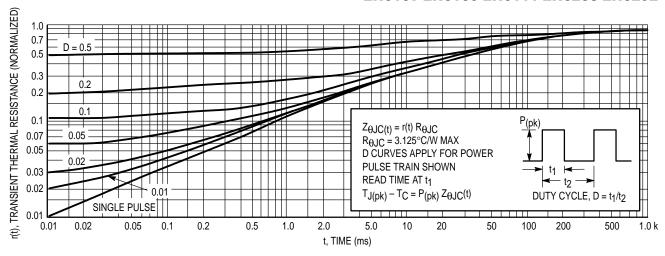


Figure 4. Thermal Response

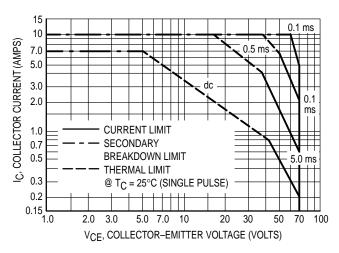


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

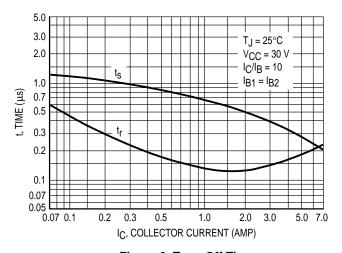


Figure 6. Turn-Off Time

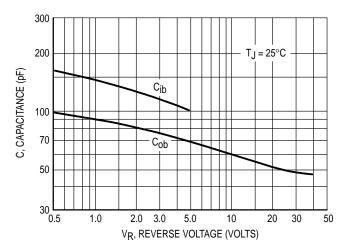
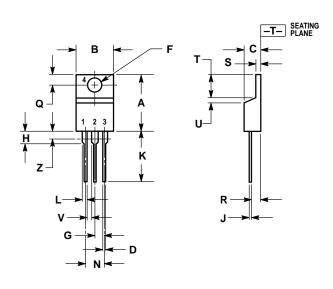


Figure 7. Capacitance

2N6107 2N6109 2N6111 2N6288 2N6292

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
C	0.160	0.190	4.07	4.82	
ם	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Η	0.110	0.155	2.80	3.93	
7	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
ø	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

STYLE 1:

PIN 1. BASE

- COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**

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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



